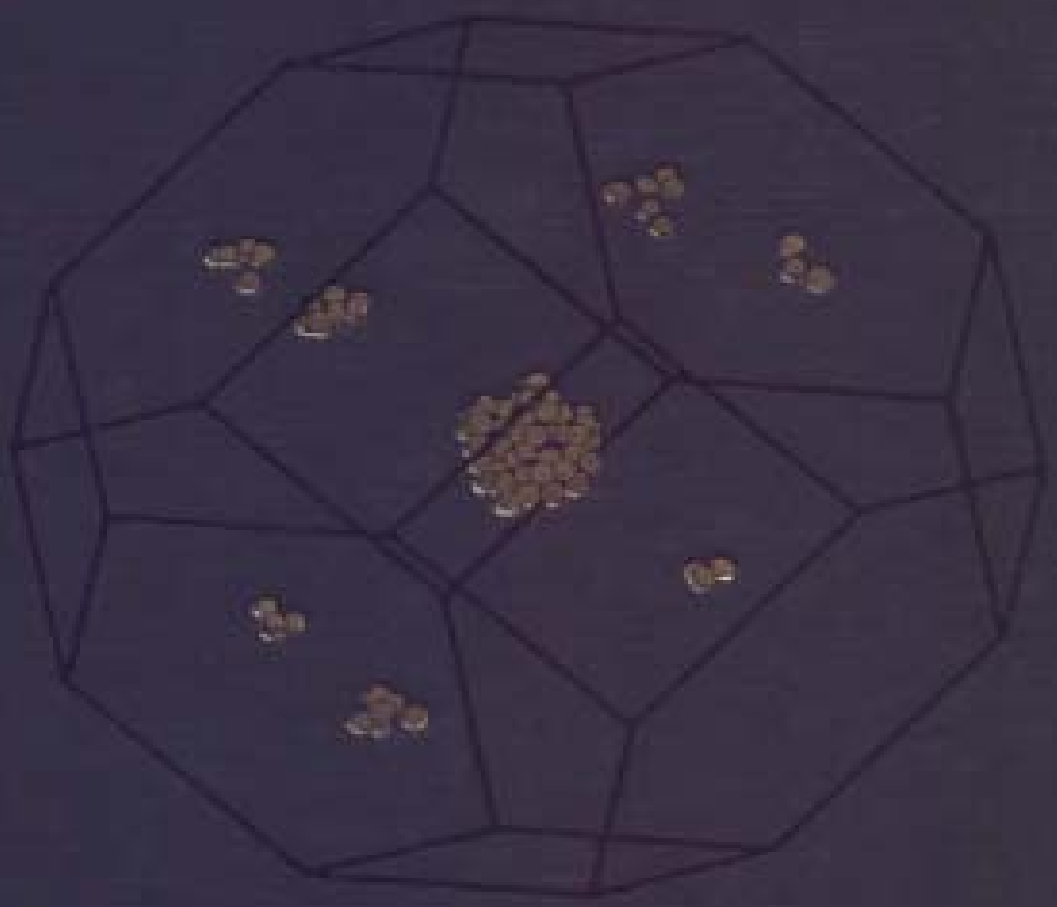
COMPOUND SEMICONDUCTOR DEVICE PHYSICS



Sandip Tiwari

Contents

Preface xv

1 Introduction 1
1.1 Outline of the Book 2
1.2 Suggested Usage 4
1.3 Comments on Nomenclature 5

2 Review of Semiconductor Physics, Properties, and Device Implications 7
2.1 Introduction 7
2.2 Electrons, Holes, and Phonons 9
2.3 Occupation Statistics 26
2.3.1 Occupation of Bands and Discrete Levels 26
2.3.2 Band Occupation in Semiconductors 32
2.4 Band Structure 36
2.5 Phonon Dispersion in Semiconductors 43
2.6 Scattering of Carriers 47
2.6.1 Defect Scattering 49
2.6.2 Carrier–Carrier Scattering 51
2.6.3 Lattice Scattering 52
2.6.4 Phonon Scattering Behavior 53
2.7 Carrier Transport 54
2.7.1 Majority Carrier Transport 55
2.7.2 Two-Dimensional Effects on Transport 70
2.7.3 Minority Carrier Transport 72
2.7.4 Diffusion of Carriers 76
2.8 Some Effects Related to Energy Bands 78
2.8.1 Avalanche Breakdown 79
2.8.2 Zener Breakdown 90
2.8.3 Density of States and Related Considerations 92

2.8.4 Limiting and Operational Velocities of Transport . . 95
2.8.5 Tunneling Effects 99
2.9 Summary 100
General References 101
Problems 102

3 Mathematical Treatments 105
3.1 Introduction 105
3.2 Kinetic Approach 107
3.3 Boltzmann Transport Approach 113
3.3.1 Relaxation Time Approximation 116
3.3.2 Conservation Equations 122
3.3.3 Limitations 128
3.4 Monte Carlo Transport Approach 135
3.5 Drift-Diffusion Transport 149
3.5.1 Quasi-Static Analysis 153
3.5.2 Quasi-Neutrality 153
3.5.3 High Frequency Small-Signal Analysis 157
3.6 Boundary Conditions 163
3.6.1 Shockley Boundary Conditions 163
3.6.2 Fletcher Boundary Conditions 166
3.6.3 Misawa Boundary Conditions 168
3.6.4 Dirichlet Boundary Conditions 170
3.6.5 Neumann Boundary Conditions 172
3.7 Generation and Recombination 173
3.7.1 Radiative Recombination 174
3.7.2 Hall–Shockley–Read Recombination 175
3.7.3 Auger Recombination 180
3.7.4 Surface Recombination 182
3.7.5 Surface Recombination with Fermi Level Pinning . . 186
3.8 Summary 190
General References 191
Problems 193

4 Transport Across Junctions 199
4.1 Introduction 199
4.2 Metal–Semiconductor Junctions 200
4.2.1 Drift-Diffusion 208
4.2.2 Thermionic Emission 211
4.2.3 Field Emission and Thermionic Field Emission . . . 214
4.2.4 Thermionic Emission-Diffusion theory 219
4.3 Heterojunctions 222

4.3.1 Thermionic Emission 226
4.3.2 Tunneling 231
4.3.3 Resonant Fowler–Nordheim Tunneling 239
4.4 Ohmic Contacts 241
4.5 p–n Junctions 248
4.5.1 Depletion Approximation 248
4.5.2 High-Level Injection 252
4.5.3 Gummel–Poon Quasi-Static Model 257
4.5.4 Abrupt and Graded Heterojunction p–n Diodes . . . 280
4.6 Summary 292
General References 292
Problems 293

5 Metal–Semiconductor Field Effect Transistors 299
5.1 Introduction 299
5.2 Analytic Quasi-Static Models 301
5.2.1 Gradual Channel Approximation 302
5.2.2 Constant Mobility Model 302
5.2.3 Constant Velocity Model 308
5.3 Constant Mobility with Saturated Velocity Model 311
5.3.1 Transconductance 324
5.3.2 Output Conductance 326
5.3.3 Gate-to-Source Capacitance 327
5.3.4 Gate-to-Drain Capacitance 327
5.3.5 Drain-to-Source Capacitance 329
5.4 Accumulation–Depletion of Carriers 330
5.5 Sub-Threshold and Substrate Injection Effects 339
5.6 Sidegating Effects 340
5.6.1 Injection and Conduction Effects 341
5.6.2 Bulk-Dominated Behavior 348
5.6.3 Surface-Dominated Behavior 354
5.7 Piezoelectric Effects 356
5.8 Signal Delay along the Gate 363
5.9 Small-Signal High Frequency Models 365
5.10 Limit Frequencies 385
5.11 Transient Analysis 390
5.12 Off-Equilibrium Effects 392
5.13 Summary 394
General References 397
Problems 398

6 Insulator and Heterostructure Field Effect Transistors 403
6.1 Introduction 403
6.2 Heterostructures 405
6.3 Strained Heterostructures 408
6.4 Band Discontinuities 410
6.5 Band Bending and Subband Formation 412
6.6 Channel Control in HFETs 426
6.7 Quasi-Static Insulator FET Analysis 432
6.7.1 Capacitance of the MIS Structure 447
6.7.2 Flat-Band Voltage 449
6.7.3 MISFET Models Based on Sheet Charge Approximation 451
6.8 HFET Analysis 483
6.8.1 Sub-Threshold Currents 501
6.8.2 Intrinsic Capacitances 502
6.8.3 Transconductance 506
6.9 Quasi-Static Circuit Refinements 506
6.10 Small-Signal Analysis 509
6.11 Transient Analysis 520
6.12 Hot Carrier Injection Effects 522
6.13 Effects Due to DX Centers 528
6.14 Off-Equilibrium Effects 535
6.15 p-channel Field Effect Transistors 540
6.16 Summary 541
General References 542
Problems 542

7 Heterostructure Bipolar Transistors 551
7.1 Introduction 551
7.2 Quasi-Static Analysis 554
7.2.1 Extended Gummel–Poon Model 558
7.2.2 Ebers–Moll Model 575
7.3 Heterostructure Implications 580
7.3.1 Charge Transport and Storage in the Base–Emitter Junction 589
7.3.2 Alloy Grading, Doping Design and Transport at the Base–Emitter Junction 591
7.3.3 Base–Emitter Capacitance 598
7.3.4 Electron Quasi-Fields in Single Heterojunction Bipolar Transistors 602
7.4 High Current Considerations 604

7.4.1 Barriers and their Influence in Heterojunction Collectors . . . 604
7.4.2 Collector Electron Quasi-Fields . . . 610
7.4.3 Diffusion Capacitances . . . 612
7.4.4 Current Gain Effects . . . 615
7.5 Generation and Recombination Effects . . . 616
7.5.1 Bulk Effects . . . 618
7.5.2 Surface Effects . . . 620
7.5.3 Current Gain Behavior . . . 626
7.6 Small-Signal Analysis . . . 629
7.6.1 Parameter Notation and Assumptions . . . 631
7.6.2 Static and Small-Signal Solutions . . . 637
7.6.3 Network Parameters and their Approximations . . . 645
7.6.4 Frequency Figures of Merit . . . 664
7.7 Small-Signal Effects of Alloy Grading . . . 672
7.8 Transit Time Resonance Effects . . . 681
7.9 Transient Analysis . . . 683
7.10 Off-Equilibrium Effects . . . 684
7.11 Summary . . . 698
General References . . . 699
Problems . . . 700

8 Hot Carrier and Tunneling Structures 705
8.1 Introduction . . . 705
8.2 Quantum-Mechanical Reflections . . . 709
8.3 Hot Carrier Structures . . . 714
8.4 Resonant and Sequential Tunneling . . . 723
8.5 Transistors with Coupled Barrier Tunneling . . . 743
8.6 Summary . . . 746
General References . . . 747
Problems . . . 748

9 Scaling and Operational Limitations 755
9.1 Introduction . . . 755
9.2 Operational Generalities . . . 757
9.3 General Scaling Considerations . . . 761
9.4 Limits from Operational Considerations . . . 765
9.5 Scaling and Operational Considerations of FETs . . . 767
9.5.1 Limitations from Transport . . . 776
9.6 Scaling and Operational Considerations of HBTs . . . 779
9.7 Summary . . . 780

General References 781
Problems 782

A Network Parameters and Relationships 783

B Properties of Compound Semiconductors 791

C Physical Constants, Units, and Acronyms 803

Glossary 807

Index 819